

Features

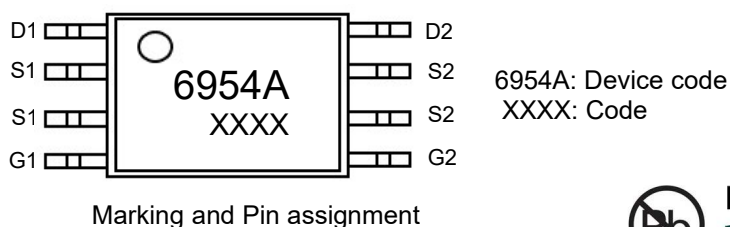
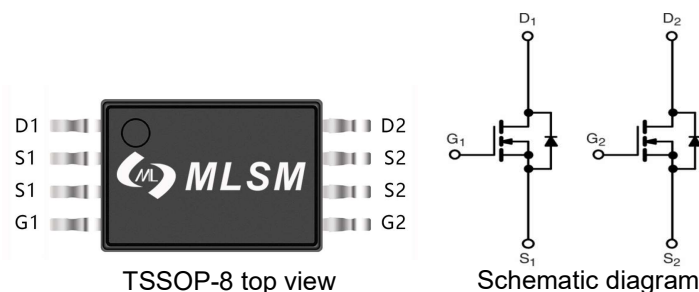
- Trench Power LV MOSFET technology
- High Power and current handing capability

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	53mΩ@10V	3.4A
	75mΩ@4.5V	

Application

- Power management
- Portable equipment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C	3.4	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	15	A
I _D	Continuous Drain Current	Tc=25°C	3.4	A
P _D	Maximum Power Dissipation	Tc=25°C	0.35	W
R _{θJA}	Thermal Resistance Junction-Ambient		357	°C/W

Ordering Information (Example)						
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSS6954A	TSSOP-8	6954A	3,000	6,000	42,000	13"reel



Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =3.4A	--	44	53	mΩ
		V _{GS} =4.5V, I _D =3.0A	--	62	75	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	230	--	pF
C _{OSS}	Output Capacitance		--	40	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	17	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =15V, I _D =3.4A, V _{GS} =10V	--	4	--	nC
Q _{gs}	Gate Source Charge		--	0.75	--	nC
Q _{gd}	Gate Drain Charge		--	0.65	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, R _L =3.6Ω, V _{GS} =4.5V, R _G =6Ω	--	10	--	nS
t _r	Turn-on Rise Time		--	50	--	nS
t _{d(off)}	Turn-Off Delay Time		--	10	--	nS
t _f	Turn-Off Fall Time		--	20	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =3.4A	--	--	1.2	V

Typical Operating Characteristics

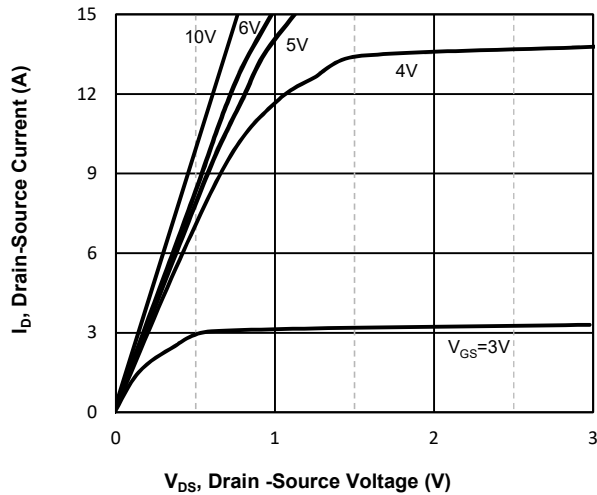


Fig1. Typical Output Characteristics

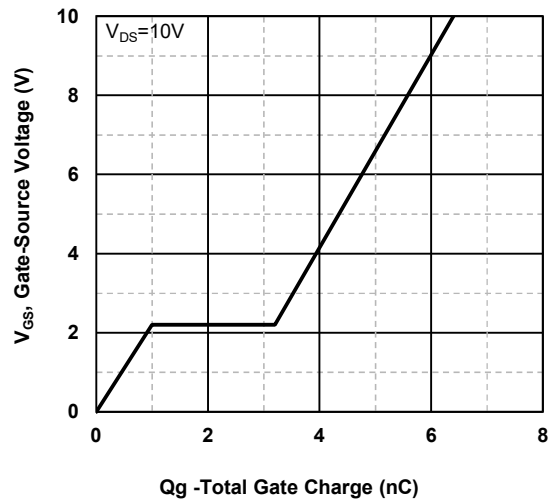


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

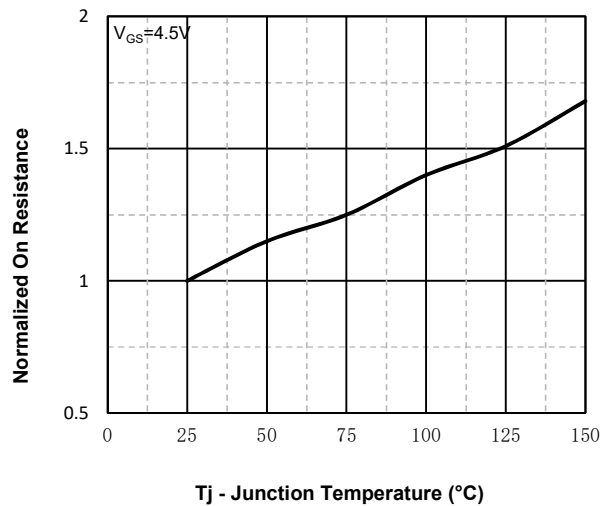


Fig3. Normalized On-Resistance Vs. Temperature

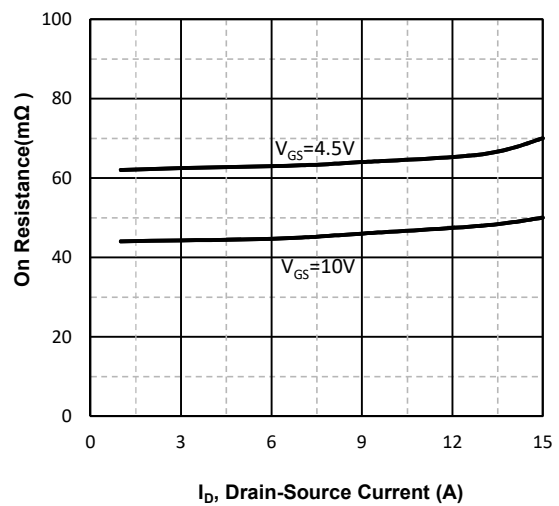


Fig4. On-Resistance Vs. Drain-Source Current

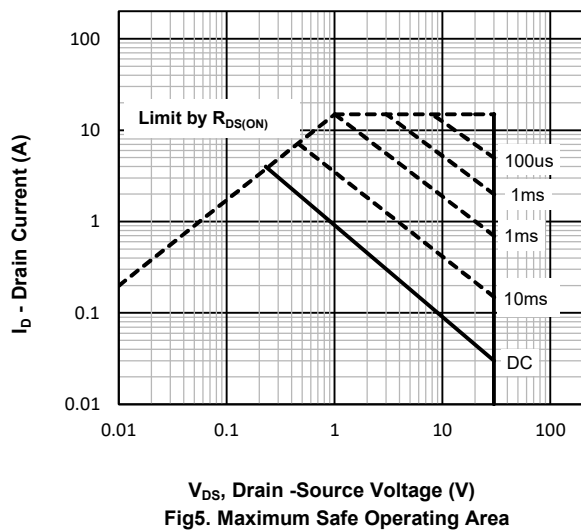


Fig5. Maximum Safe Operating Area

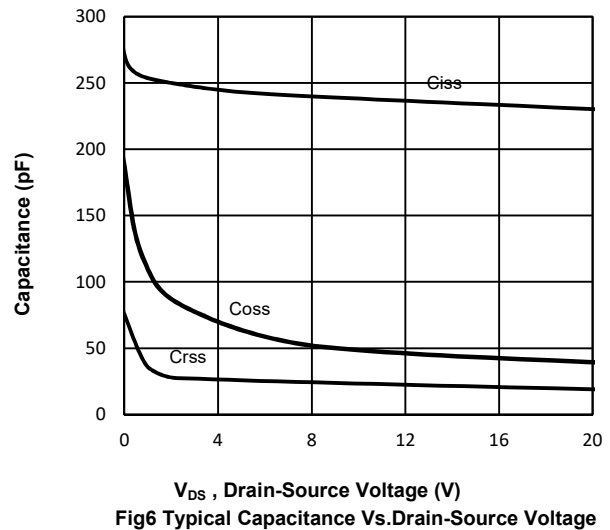
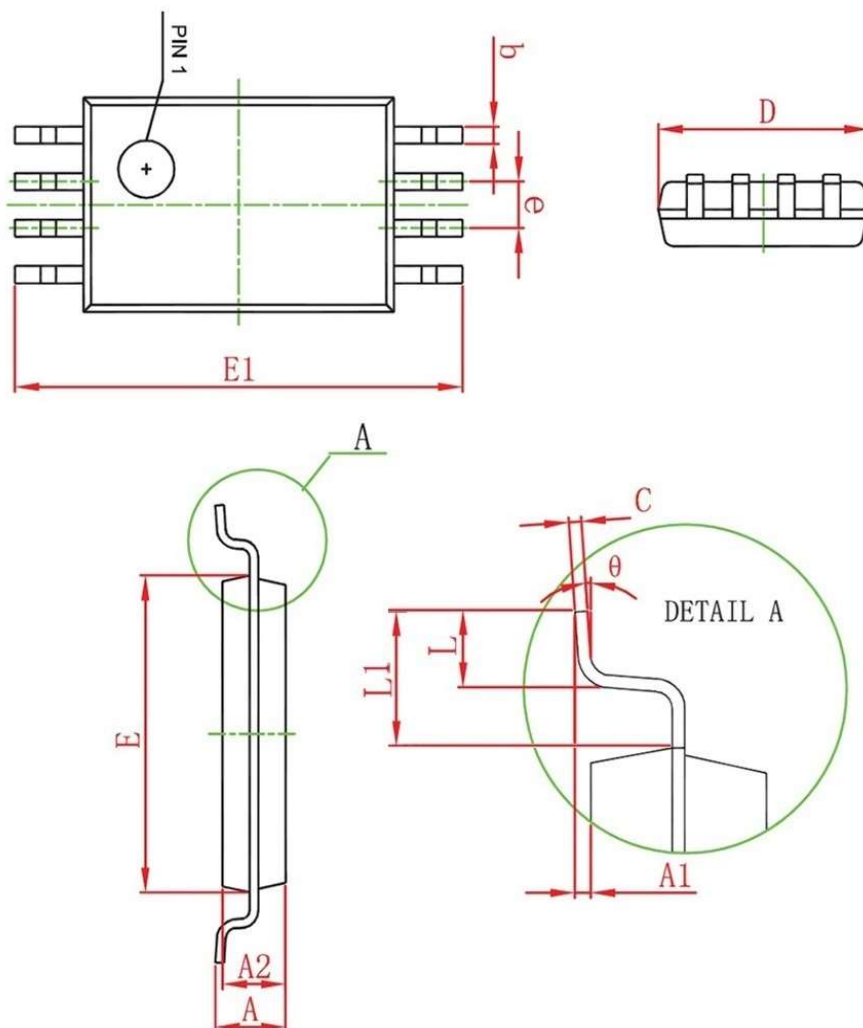


Fig6 Typical Capacitance Vs. Drain-Source Voltage

TSSOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	1.000	1.200	0.039	0.047
A1	0.020	0.180	0.000	0.007
A2	0.900	1.100	0.035	0.043
b	0.170	0.270	0.006	0.010
c	0.122	0.132	0.004	0.005
D	2.870	3.070	0.112	0.120
e	0.65BSC		0.025BSC	
E	4.300	4.500	0.169	0.177
E1	6.200	6.600	0.244	0.259
L	0.400	0.800	0.015	0.031
L1	1.00BSC		0.039BSC	
Ø1	0.500	0.700	0.001	0.027
θ	0°	10°	0°	10°